

Title (en)

SEMICONDUCTOR JUNCTION CAPACITOR IN INTEGRATED METHOD OF CONSTRUCTION AND BOOTSTRAP CIRCUIT WITH SUCH A CAPACITOR

Publication

**EP 0000169 B1 19811007 (DE)**

Application

**EP 78100194 A 19780619**

Priority

US 81102877 A 19770629

Abstract (en)

[origin: US4191899A] An integrated circuit junction capacitor is formed using conventional bipolar transistor technology. Voltage variable capacitance is provided by a reverse biased emitter-base junction and parasitic collector-base capacitance is isolated from the emitter-base capacitance by maintaining the base-collector junction in a reverse biased condition. A bootstrapped driver circuit is also described in which bootstrap current is provided by a transistor-like structure in which an internal load capacitance enables circuit performance to remain substantially constant under various driven load conditions.

IPC 1-7

**H01L 27/08**; **H03K 19/003**

IPC 8 full level

**H01L 21/331** (2006.01); **H01L 21/822** (2006.01); **H01L 27/04** (2006.01); **H01L 27/07** (2006.01); **H01L 27/08** (2006.01); **H01L 29/73** (2006.01); **H01L 29/93** (2006.01); **H03K 19/013** (2006.01); **H03K 19/018** (2006.01); **H03K 19/082** (2006.01)

CPC (source: EP US)

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Cited by

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DOCDB simple family (publication)

**EP 0000169 A1 19790110**; **EP 0000169 B1 19811007**; DE 2861127 D1 19811217; IT 1112275 B 19860113; IT 7825052 A0 19780628; JP S5412577 A 19790130; JP S5635028 B2 19810814; US 4191899 A 19800304

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